STARPOWER

SEMICONDUCTOR

Rectifier Diode

RD100HFS160C1S

Molding Type Module

1600V/100A 2 in one-package

General Description

STARPOWER Rectifier Diode Power Module provides ultra low conduction loss. They are designed for the applications such as SMPS.

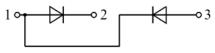
Features

- Planar Passivated Chips
- High Surge Capacity
- Dual Diodes Cascaded Circuit
- Isolated Copper Baseplate Using DBC Technology

Typical Applications

- Input bridge rectifier
- AC/DC motor control
- Power supply





Equivalent Circuit Schematic

Symbol	Description	RD100HFS160C1S	Units	
V _{RRM}	Repetitive Peak Reverse Voltage	1600	V	
V _{RSM}	Non-repetitive Peak Reverse Voltage	1700	V	
I _{F(AV)}	Average On-state Current @ T _C =100°C	115	Α	
I _{FSM}	Surge Current $t_p=10ms(50Hz), T_j=45^{\circ}C$, sine	1800		
	$t_p=8.3ms(60Hz), T_j=45$ °C, sine	1850	А	
	$t_p=10ms(50Hz), T_i=150$ °C, sine	1560	A	
	$t_p = 8.3 \text{ms}(60 \text{Hz}), T_j = 150^{\circ}\text{C}, \text{sine}$	1700		
I ² t-value	$t_p=10ms(50Hz), T_i=45$ °C, sine	16200	A ² s	
	$t_p=8.3ms(60Hz), T_j=45^{\circ}C$, sine	14260		
	$t_p=10ms(50Hz), T_j=150$ °C, sine	12170		
	$t_p=8.3ms(60Hz), T_i=150^{\circ}C$, sine	12040		
T _{jmax}	Maximum Junction Temperature	150	°C	
T _{jop}	Operating Junction Temperature	-40 to +125	°C	
T _{STG}	Storage Temperature Range	-40 to +125	°C	
V _{ISO}	Isolation Voltage RMS,f=50Hz,t=1min	3400	V	
Mounting	Power Terminal Screw:M5	2.5 to 5.0	N.m	
Torque	Mounting Screw:M6	3.0 to 5.0		
Weight	Weight of Module	150	g	

Absolute Maximum Ratings $T_{\rm C}{=}25\,^\circ\!{\rm C}$ unless otherwise noted

Electrical Characteristics of Diode T_c=25[°]C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
$V_{\rm F}$	Diode Forward	I _F =200A	Tj=25℃			1.25	v
	Voltage		T _j =150℃			1.20	
I _R	Diode Reverse	V _R =V _{RRM}	$T_j=150$ °C			2.0	mA
	Current						
L _{CE}	Stray Inductance					30	nH
R _{CC'+EE'}	Module Lead						
	Resistance,	T _C =25 ℃			0.75		mΩ
	Terminal To Chip						

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (per Diode)		0.336	K/W
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.05		K/W

RD100HFS160C1S

Rectifier Diode Module

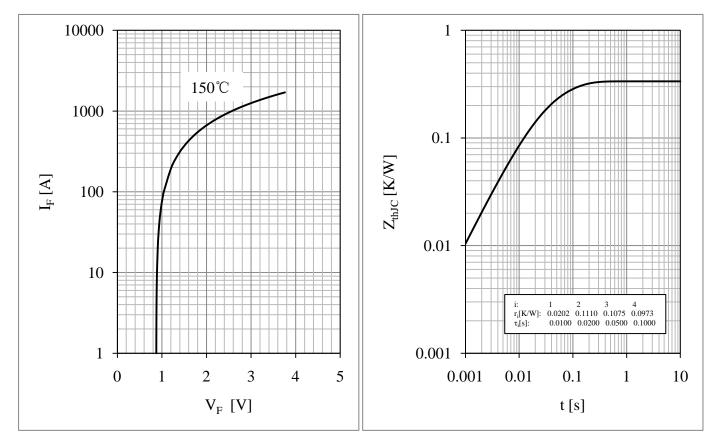


Fig 1. Diode Forward Characteristic

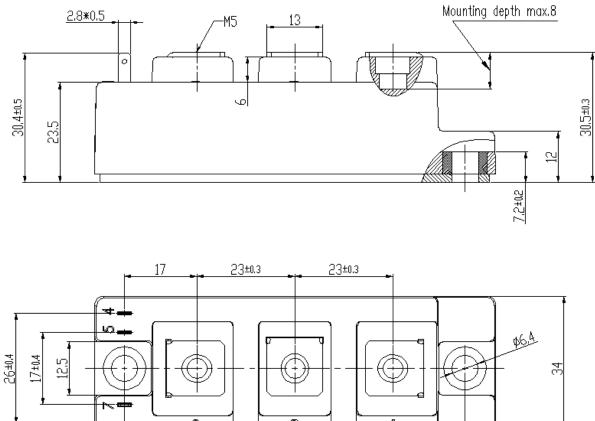
Fig 2. Diode Transient Thermal Impedance

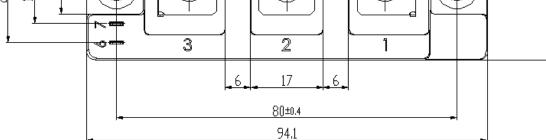
RD100HFS160C1S

Rectifier Diode Module

Package Dimensions

Dimensions in Millimeters





©2012 STARPOWER Semiconductor Ltd. 7/10/2012 4/5 Rev.A

Terms and Conditions of Usage

The data contained in this product datasheet is exclusively intended for technically trained staff. you and your technical departments will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to such application.

This product data sheet is describing the characteristics of this product for which a warranty is granted. Any such warranty is granted exclusively pursuant the terms and conditions of the supply agreement. There will be no guarantee of any kind for the product and its characteristics.

Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of our product, please contact the sales office, which is responsible for you (see <u>www.powersemi.cc</u>), For those that are specifically interested we may provide application notes.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the Product in aviation applications, in health or live endangering or life support applications, please notify.

If and to the extent necessary, please forward equivalent notices to your customers. Changes of this product data sheet are reserved.